

Structural, Optical and Microwave Dielectric Properties of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$, $0 \leq x \leq 0.7$ Ceramics

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Research Article

Keywords: X-ray diffraction (XRD), Grain size, Scanning electron microscopy (SEM, Optical properties), Dielectric properties.

Posted Date: June 7th, 2021

DOI: <https://doi.org/10.21203/rs.3.rs-566760/v1>

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Abstract

Sn-doped BaTi₄O₉ (BT4) microwave ceramics were prepared by a mixed oxide route. Preliminary X-ray diffraction (XRD) structural study shows that the samples have orthorhombic symmetry with space group (Pnmm). Scanning electron microscopy (SEM) shows that the grain size of the samples decreases with increasing Sn⁴⁺ contents. The presence of the metal oxide efficient group was revealed by Fourier transform infrared (FTIR) spectroscopy. The Photoluminescence spectra of the samples reported red color ~ 603, 604, 606.5 and 605 nm with excitation energy ~ 2.06, 2.05, 2.04 and 2.05 eV for Sn content at x = 0.0, 0.3, 0.5, and 0.7, respectively. The microwave dielectric properties of all the samples were investigated by an impedance analyzer. The excellent microwave dielectric properties i.e. high relative permittivity ($\epsilon_r = 57.29$), high-quality factor ($Q_f = 11,852$), and low-dielectric loss (3.007) has been observed.

Introduction

Dielectric materials are frequently used in modern telecommunication systems like satellite modules and cellular phones. Dielectric layered-structured materials have been widely investigated for their potential use in ferroelectric random access memories (FeRAM) and piezoelectric devices. Ferroelectric and piezoelectric ceramics are broadly used in a range of applications such as sensors, actuators, transducers, pulse signal circuits, spacecraft, X-ray equipment, weapons, medical devices, and transportation. The dielectric component used in these devices is termed dielectric resonators (DR). The optimum commercial properties of these ceramics included the excellent dielectric constant (ϵ_r), good quality factor (Q_f) or low tangent loss ($\tan \sigma$), and near to zero temperature coefficient at resonant frequency (τ_f)¹⁻⁶. For example, a dielectrically loaded antenna requires; ϵ_r from 20 to 85, (Q) $\geq 10,000$, and τ_f close to zero^{7,8}. Some time quality factors can be expressed in the product of Q and f_o (resonant frequency) i.e. ($Q \times f_o$). The dielectric constant and dielectric loss ($\tan \sigma$) decreases with a resonant frequency, which suggests that electric dipoles and interfaces play a key role at lower frequencies. The decrease in dielectric constant with resonant frequency can be explained based on Koops theory reported by K. Praveena and K. B. R. Varma⁹. A relatively good dielectric constant is required for the miniaturization of devices and low tangent loss is required for noise reduction while zero τ_f is important for temperature stability of the DR². From the manufacturing point of view, it is very difficult to obtain compounds with all three optimum properties along with a low cost. Among oxides compounds, BaTi₄O₉ (BT4) is one of the dielectric materials that may be used in the microwave domain reported first by Rase and Roy¹⁰. It has been recorded that BaTi₄O₉ ceramics have $\epsilon_r = 37.3$, $Q = 27200$ GHz and $\tau_f = +15$ ppm/ $^{\circ}\text{C}$ ¹¹. On the other side, wet chemical methods (i.e. sol-gel, co-precipitation, or hydrothermal) can be used for the preparation of titanates ceramics¹². The optical, structural, microstructural, and microwave properties of BaTi₄O₉ ceramic samples with various dopant elements have been studied at microwave frequency. Many researchers studied the effects of B site cation substitutions. Dielectric properties of the sample may be affected by the substitution of larger ionic radius (Sn⁴⁺) for smaller ionic radius (Ti⁴⁺)

ions¹³⁻¹⁵. In this way Veenhuis et al processed compounds with good dielectric properties which have been used in the field of advanced laser technology and optical storage devices¹⁶.

In the present decade, BT4 has been investigated broadly because of its good Q_f , high ϵ_r , and small τ_f . Hence, widely used in microwave dielectric resonator applications, patch antenna, microwave telecommunication, etc. During the densification of these titanates at very high sintering temperatures, enhanced dielectric properties are observed due to the structural and compositional defects (fluctuations) because of the substitution of Ti^{4+} ion for Ti^{3+} ion¹⁷. The present work aims to achieve a material with enhanced structural and electrical properties for device application. In this report, we describe the preparation of $Ba(Ti_{1-x}Sn_x)_4O_9$ ceramics by the mixed oxide method. The calcined powders and sintered products obtained were characterized by XRD (X-ray diffraction), SEM (scanning electron microscopy), impedance analyzer, and FTIR (Fourier transform infra-red). The microwave dielectric properties of samples are discussed in terms of their physical and chemical characteristics.

Materials And Methods

The starting raw materials were: $BaCO_3$ (Merck, Germany, 99.9%), TiO_2 (Aldrich Chemical Company, Inc., U.S.A, 99.9%), and SnO_2 (Strem, Chemicals, U.S.A, 99.9%) to make solid solutions of $Ba(Ti_{1-x}Sn_x)_4O_9$, $0 \leq x \leq 0.7$ by the conventional mixed oxides route. These raw materials were balanced according to stoichiometric ratio and mixed for 12 hours in distilled water by using horizontal ball milling. Then the slurry was dried in a microwave oven at 100 °C for one day and calcined at 1100 °C for 3 h in a nickel crucible in the air atmosphere with a heating-cooling rate of 10 °C/min. The calcined powders were grinded for 60 mins with a mortar and pistol manually to avoid agglomerations. Then pressed 0.6-0.8 gm of powder into cylindrical pellets of thickness 2 mm and diameter 10 mm by using a hydraulic press (CARVER, USA) with a pressure of 80 MPa. Thereafter the pellets were sintered at 1320 °C temperature in the open air for 2 h with a heating-cooling rate of 10 °C/min. The XRD patterns of the compounds were recorded at room temperature using an X-ray powder diffractometer (JDX-3532, JEOL, Japan) with Cu Ka radiation ($k = 1.5405 \text{ \AA}$) in a wide range of Bragg angles 2θ ($20^\circ \leq 2\theta \leq 60^\circ$) at a scanning rate of 2 deg min^{-1} . The experimental density of the samples was measured by the archimedes principle using a density meter (MD-3005, Germany). Scanning electron microscopy (SEM, JEOL 7600F) can be used to study the microstructure of the dense pellets. To obtain 10 cm^{-1} resolution spectra of the pellets were carried out by using the Fourier transformation infrared spectroscopy (FTIR, Perkin-Elmer).

Results And Discussions

XRD analysis

Figure 1 represents the room temperature XRD patterns of $Ba(Ti_{1-x}Sn_x)_4O_9$, $0 \leq x \leq 0.7$ ceramics. The mean peaks corresponding to (200), (121), (150), (211), (230), (320), (213), and (503) planes are well-matched with PDF card number 34-70 of $BaTi_4O_9$ ceramics and have an orthorhombic structure with

space group (Pnmm). Some of the secondary phases of Ba₂Ti₈O₁₈ are detectable and matched with PDF card number 0080-0916. It can be noted from Figure 1 that the peaks shifted toward the lower 2θ values representing expansion in the lattice cell volume as the Sn⁴⁺ contents increase in ceramics. This might be due to the inhomogeneity, microstrain, or maybe due to the substitution of the relatively larger cation ion of Sn⁴⁺ (~0.69 Å) for a lower cation ion of Ti⁴⁺ (~0.64 Å)¹⁸. The calculated lattice parameters (i.e. 'a', 'b', and 'c') from the X-ray diffraction show increase in their values as Sn⁴⁺ content increased. This increase in the lattice parameters, resulting in the phase transition from orthorhombic to a tetragonal structure. The average crystallite size of each ceramics was calculated by using Debye Scherer's formula¹⁹ and the observed average crystallite size and various lattice parameters are listed in Table 1.

$$\text{Crystallite size, } D = \frac{0.9\lambda}{\beta \cos\theta} \quad (1)$$

Microstructure analysis

SEM images were used to calculate the average grain size and density of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics (as shown in Figure 2). It can be noted that two types of morphologies present in all samples-rodlike and spherical shape particles. The relative population is increased when the Sn⁴⁺ doping content is increased in the base sample. The existence of cavities in the denser pellets confirms the existence of porosity. Thus, an increase in the relative density and decrease in the porosity was observed as the Sn content increased²⁰. The porosity of the samples was calculated using equation (2) shown in Table 2.

$$\text{Porosity} = \left(\frac{\rho_{th} - \rho_{ex}}{\rho_{th}} \right) \times 100\% \quad (2)$$

Where ρ_{th} = theoretical density and ρ_{ex} = experimental density (calculated using Archimede's principle). The observed average grain size varies in the decreasing order ~10.7 to ~2 μm as dopant content x varies from 0.0 to 0.7. At x = 0.5 Sn⁴⁺ doped BaTi₄O₉ system have smaller average grain size, gives rise to a more uniform grain size distribution with an overall average grain size of 0.8 μm. Thus, high densification (~99.4%) and low porosity (~0.55 %) were achieved with Sn⁴⁺ content which tends to reduce grain growth.

Optical properties

The FTIR spectra of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics at room temperature as shown in Figure 3. The peaks that appear near ~2852, ~2922, and ~1433 cm⁻¹ represents the symmetric, asymmetric, and bending vibrations of the -CH₂ group, respectively²¹. Peaks appearing at ~854 cm⁻¹ show the vibrational mode which relates to the stretching mode of the O-Ti-O system in the samples that confirms the presence of the BaTi₄O₉ structures²². The absorption mode appearing at ~690 cm⁻¹ shows the Ti-O stretching mode of the octahedral group in complex perovskite structure^{23,24}, as this mode appears only

in BaTi₄O₉ ceramic samples. Furthermore, the structure of the BaTi₄O₉ ceramic sample has been confirmed by the XRD result.

Photoluminescence spectroscopy of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 calcined ceramics is shown in Figure 4. This optical emission spectra are recognized as the recombination of electrons and holes in the state of transfer of carrier ions. By using equation (3), we can find the value of excitation energy of the samples.

$$E = hc/\lambda \quad (3)$$

Where, E = optical excitation energy, h = Plank's constant (~6.63 x 10⁻³⁴ Js) c = velocity of light (3 x 10⁸ m/s) and λ is the emission wavelength. Emission at photoluminescence peak of the samples were recorded at ~603, 604, 606.5 and 605 nm with excitation energy ~2.06, 2.05, 2.04 and 2.05 eV for x = 0.0, 0.3, 0.5, and 0.7 content of Sn, respectively. Photoluminescence is a multiphotonic process that is an optical energy emission occurred in the optical gap by many vibrational modes within the sample²⁵. Within the energy bandgap, the photoluminescence process confirmed that due to localizing state the order/disorder structure may be affected directly. Hence, the structural order may be increased with increasing the energy band gap²⁶. It has been recorded that a broad-emission spectrum was located at ~604 nm and have an optical excitation energy (~2.06 eV) which is smaller than the energy band gap of extremely ordered BaTi₄O₉ located at ~558 nm (~2.23 eV) which is maybe the absence of the oxygen vacancy²⁷. In the photoluminescence spectrum, the red color may occur due to the oxygen vacancy.

Microwave dielectric properties

The variation of the relative permittivity (ε_r) and tangent loss (tanδ) of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics versus frequency at room temperature is shown in Figure 5. Due to increasing frequency, the values of ε_r and tanδ decrease exponentially in the samples. The high value of ε_r at a resonant frequency can be described based on (i) according to Maxwell-Wagner's model the dielectric materials are consist of fine conductive grains which are surrounded by grain boundaries. Large polarization is caused by the motion of charge carriers from grain to grain surface, (ii) the ionic polarization, (iii) the majority is due to the crystal defects, vacancies, and grain defects etc²⁸. The increase in ε_r values with contents may be recognized by the substitution of a larger ionic radius of Sn⁴⁺ (~0.69 Å) cation for the lower ionic radius of Ti⁴⁺ (~0.64 Å) cation²⁹. To increasing the bond length of complex perovskite (i.e. AB₄O₉) the larger ionic radius cation may be substituted at B-site cation. The Sn⁴⁺ contents greatly affected the microwave dielectric properties due to high ionic polarizability^{30,31}. The maximum dielectric constant is obtained at x = 0.5 at maximum relative density (i.e. at low porosity). Because charge carriers need a medium to propagate and hence dielectric constant decreases with increasing material porosity³². Tanδ decreases with frequency due to the space charge polarization in all samples. At the lowest frequency, the maximum tangent loss occurs due to the presence of defects, impurities, and porosity in the ceramic

samples³³. The variation of quality factor (Q_f) and relative density (%) of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$ sintered ceramics as a function of composition (x) is shown in Figure 6. Initially, the quality factor decreased from 9264.49 to 5681.16 with increasing Sn^{4+} content (from 0 to 0.3). The observed decrease in the value of Q_f may be recognized due to the substitution of larger Sn^{4+} cation on the B- site, contributing to harmonic vibrational modes³⁴ and another reason may be the phase transition. Furthermore, an increase in contents leads to giving a high Q_f value, which may occur due to (i) the phonon modes of B-site harmonic (ii) relative density is increased as Sn^{4+} content increased as shown in Figure 6 (in blue color).

The variation of ac conductivity of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$, $0 \leq x \leq 0.7$ sintered ceramics versus frequency is shown in Figure 7. It is clear from the graph that ac conductivity depends upon the frequency and does not show any significant variation at the lowest frequency. The maximum value of ac conductivity at a lower frequency may be due to the rising state of localization in the hopping process. By the application of electric field, the hopping frequency of charge carrier increased which result in the highest value of ac conductivity towards the high-frequency region³⁵.

Conclusion

A compound of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$, ($0 \leq x \leq 0.7$) ceramics were fabricated through a conventional or mixed-oxide route. The average crystallite size of these ceramics lies in the range of 30-90 nm with structure change from orthorhombic (space group = $Pnmm$) to Tetragonal ($P4mm$). Sintered ceramics attained 99.5% of the theoretical density at content ($x = 0.5$) and fine grain growth. Photoluminescence confirms that the present state of localization within the bandgap may affect the structural order/disorder. The dielectric properties of sintered ceramics samples showed $\epsilon_r = 57.29$, and high $Q_f = 11,852$. The increase in ac conductivity is due to the hopping mechanism. Based on the above-obtained results, these ceramic materials can be used for filter applications.

Declarations

Acknowledgment

Author **Khaled Althubeiti** is thankful to Researcher Supporting Project (**TURSP-2020/241**) at **Taif University** for the financial support.

Author contributions

Asad Ali and Abid Zaman prepared samples and write the manuscript. Sarir Uddin helps in measurements. Zafar Iqbal supervise this research. Madan Lal and Khaled Althubeiti did the final writing-review, corrections, and editing. All the authors read and approve the final manuscript.

Competing interests

The authors declare that they have no competing interests.

Data availability

The data of this study are available from the corresponding author upon reasonable request.

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Tables

Composition (x)	Lattice parameters (Å)			Volume (Å ³)	Structure (space group)	Average crystallite size (D) nm
	a	b	c			
0.0	4.012	5.681	5.703	64.4	Orthorhombic (Pnmm)	90
0.3	4.024	4.024	4.045	65.1	Tetragonal (P4mm)	50
0.5	4.036	4.036	4.057	65.7		30
0.7	4.058	4.058	4.042	66.3		70

Table 2. Physical properties of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$, $0 \leq x \leq 0.7$ sintered ceramics.						
Composition (x)	ρ_{th} (gm/cm ³)	ρ_{ex} (gm/cm ³)	ρ_{re} (%)	ϵ_r	Porosity (%)	Average grain size (μm)
0.0	5.9	4.5	76.3	30.08	23.72	10.7
0.3	4.953	4.48	90.5	37.57	9.55	6.45
0.5	5.611	5.58	99.4	57.29	0.55	2.54
0.7	5.347	5.25	98.2	46.63	1.81	5.56

Figures

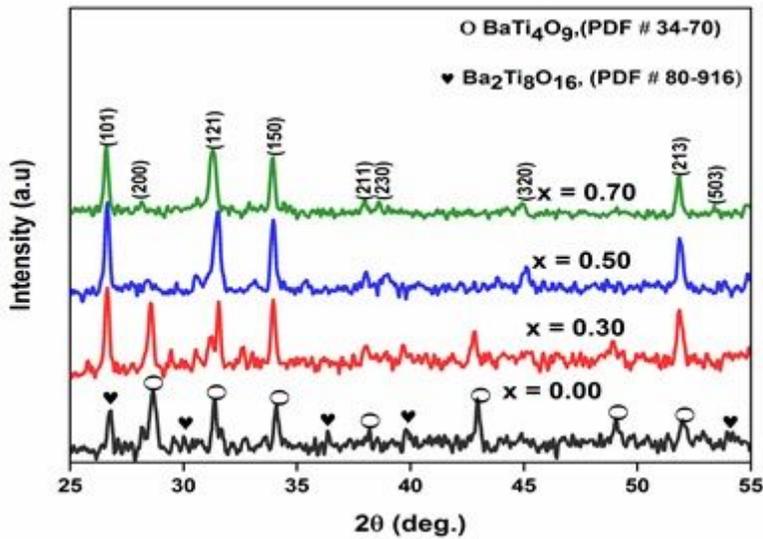


Figure 1

XRD pattern of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)_4\text{O}_9$, $0 \leq x \leq 0.7$ ceramics.

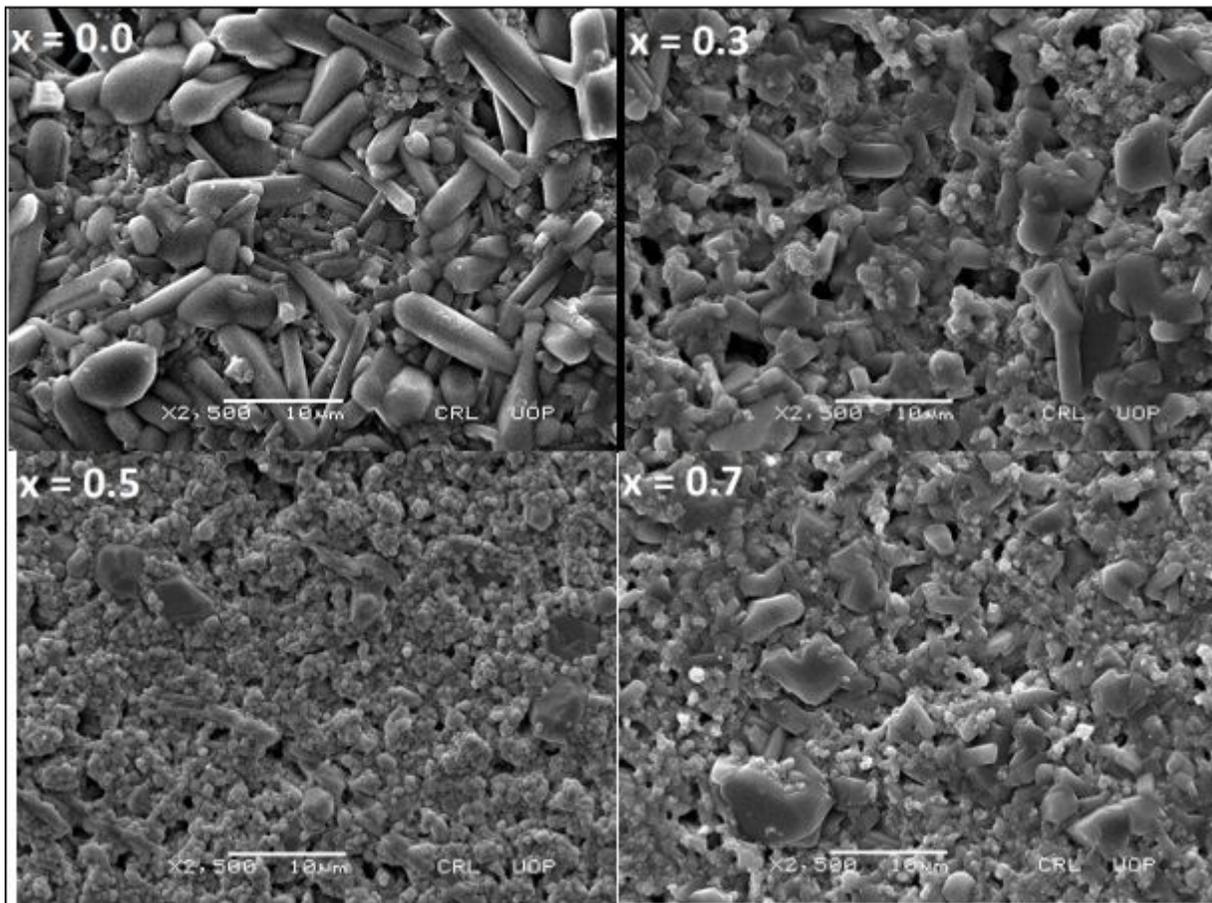


Figure 2

SEM Micrograph of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics.

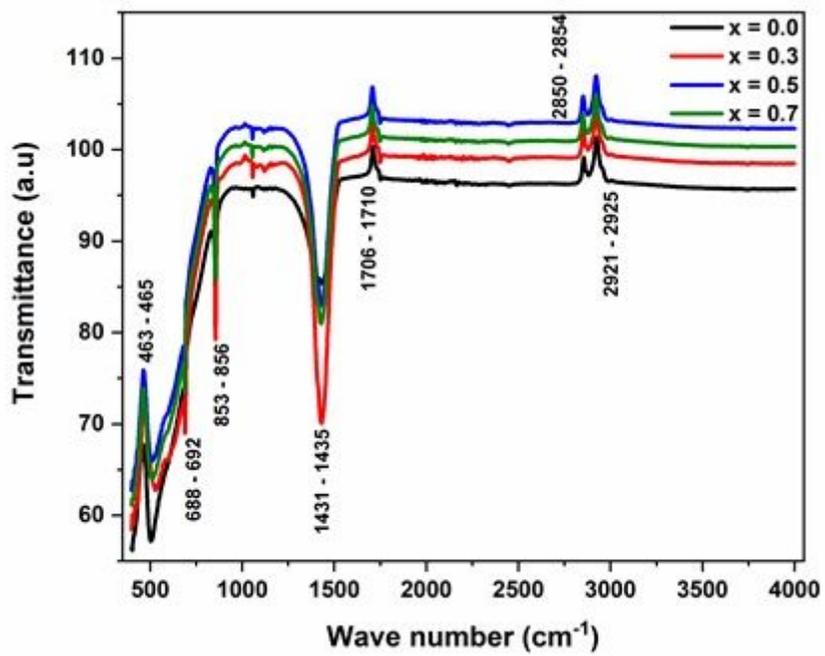


Figure 3

FTIR spectra of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics.

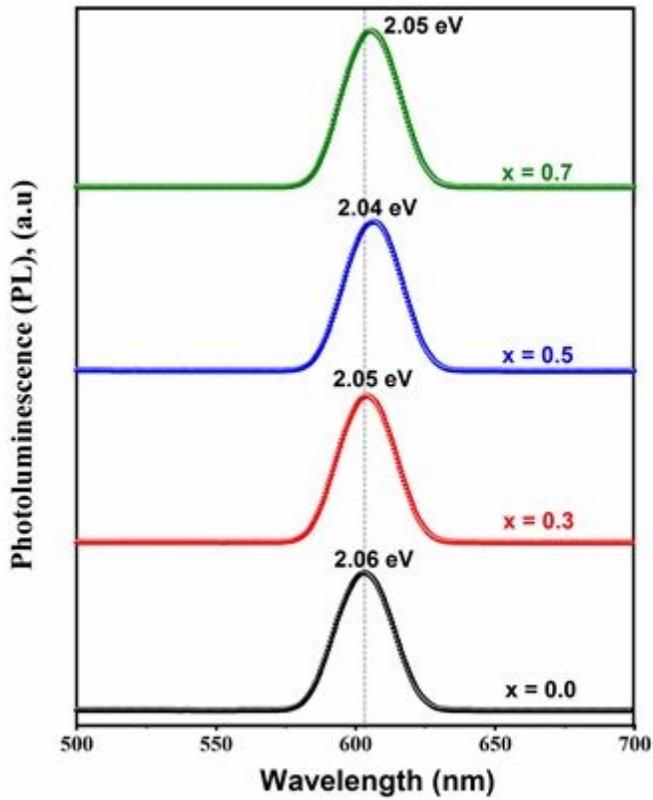


Figure 4

PL spectra of Ba(Ti_{1-x}Sn_x)₄O₉, 0 ≤ x ≤ 0.7 ceramics.

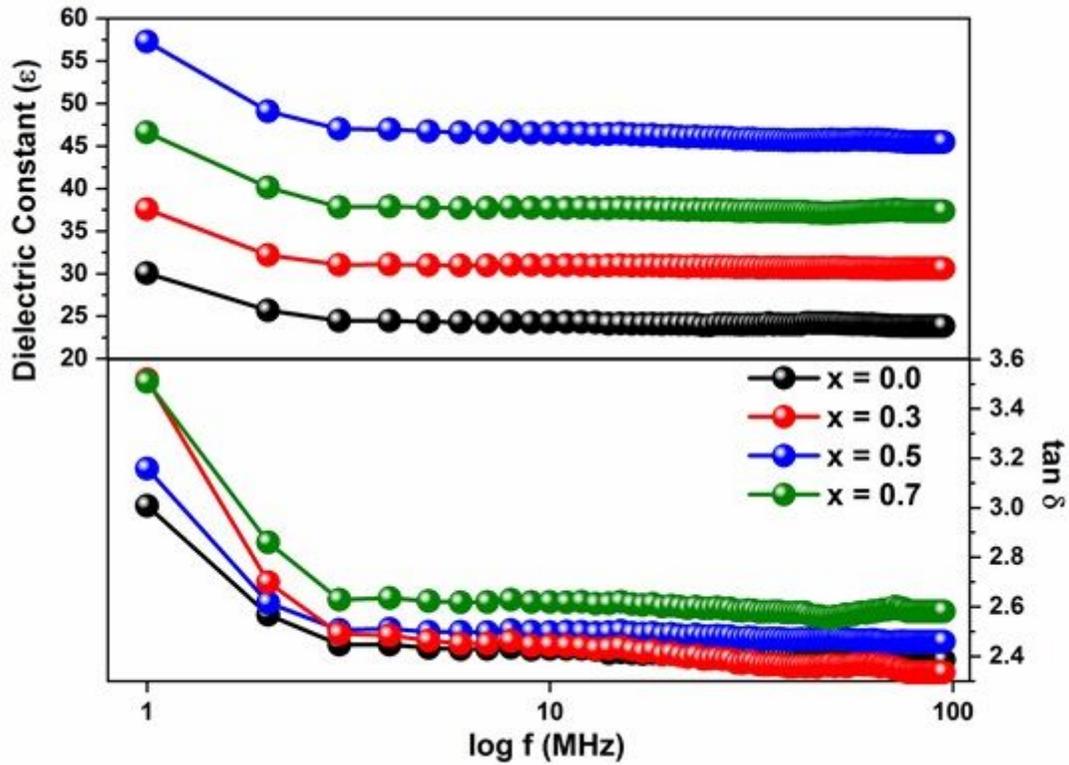


Figure 5

Frequency dependence of Dielectric constant (ϵ) and dielectric loss ($\tan\delta$) of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)\text{O}_9$, $0 \leq x \leq 0.7$ ceramics

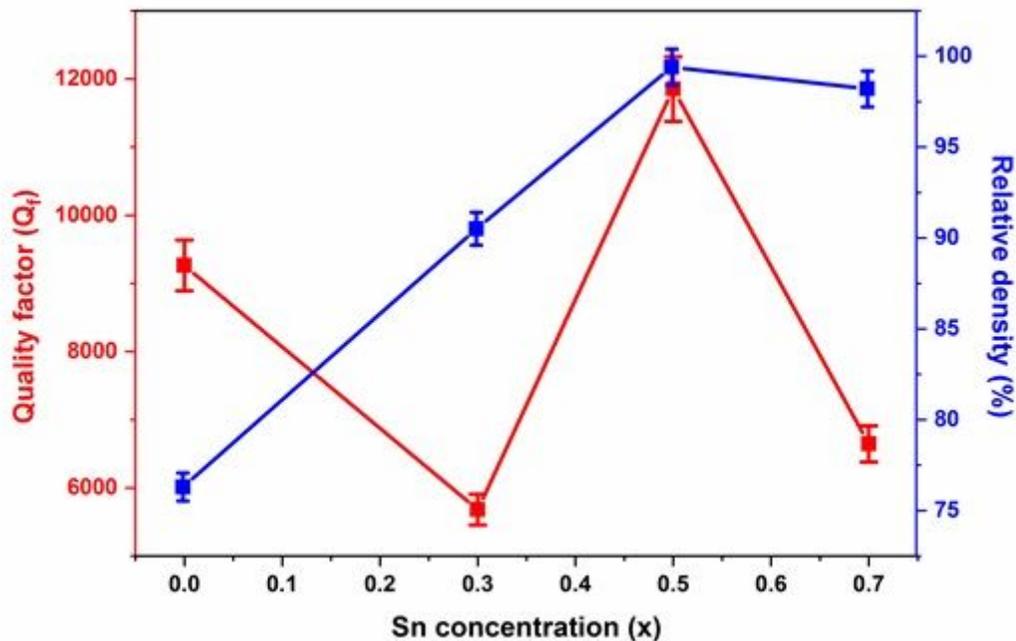


Figure 6

Variation of relative density and Quality factor (Q_f) vs Sn^{4+} contents of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)\text{O}_9$, $0 \leq x \leq 0.7$ ceramics.

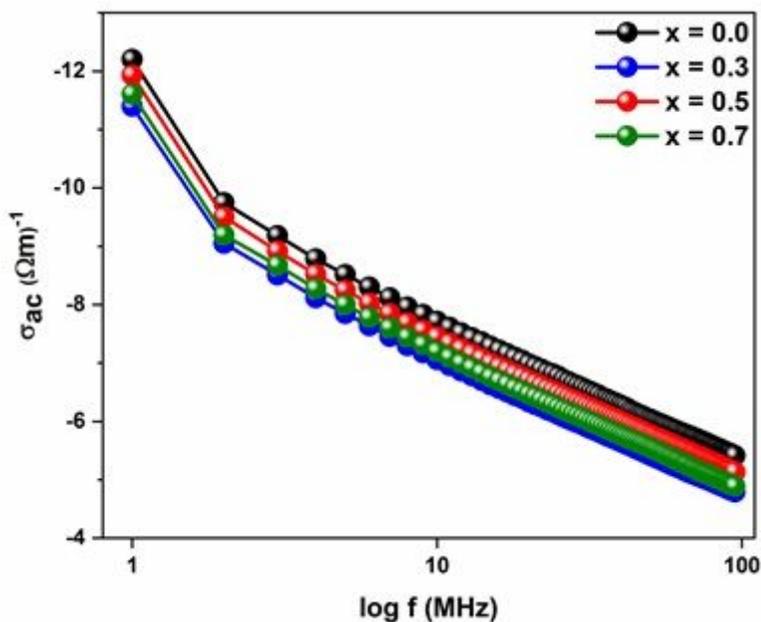


Figure 7

Variation of ac conductivity as a function of the frequency of $\text{Ba}(\text{Ti}_{1-x}\text{Sn}_x)\text{O}_9$, $0 \leq x \leq 0.7$ ceramics